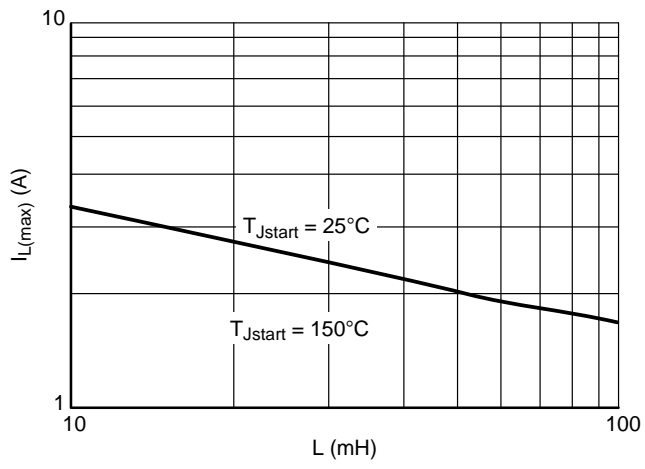




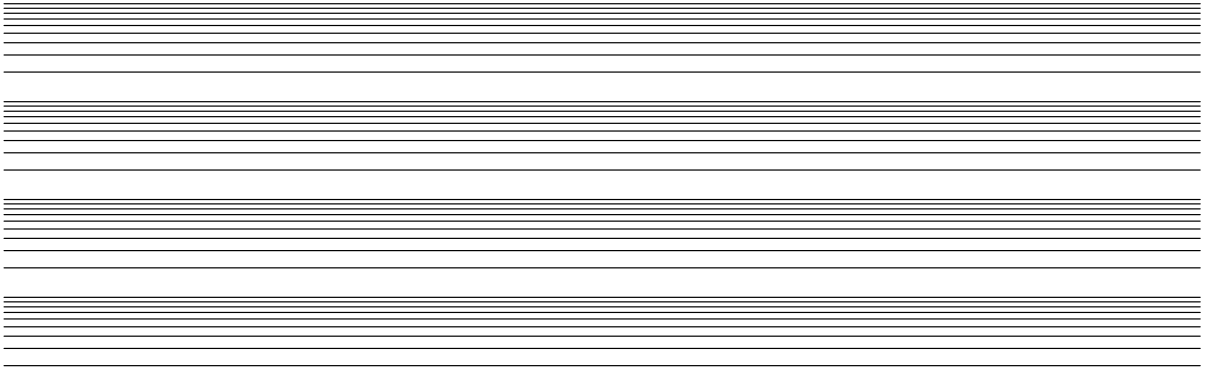
(T_J = 25°C unless otherwise noted)

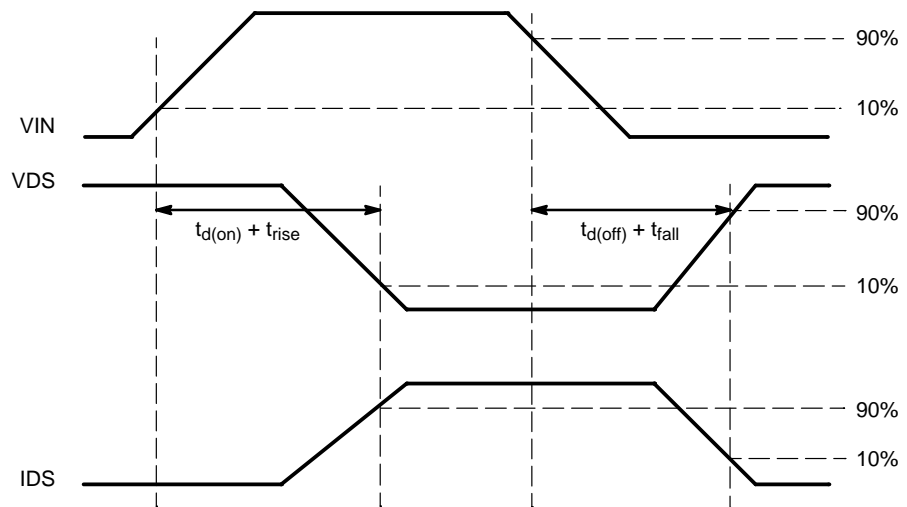
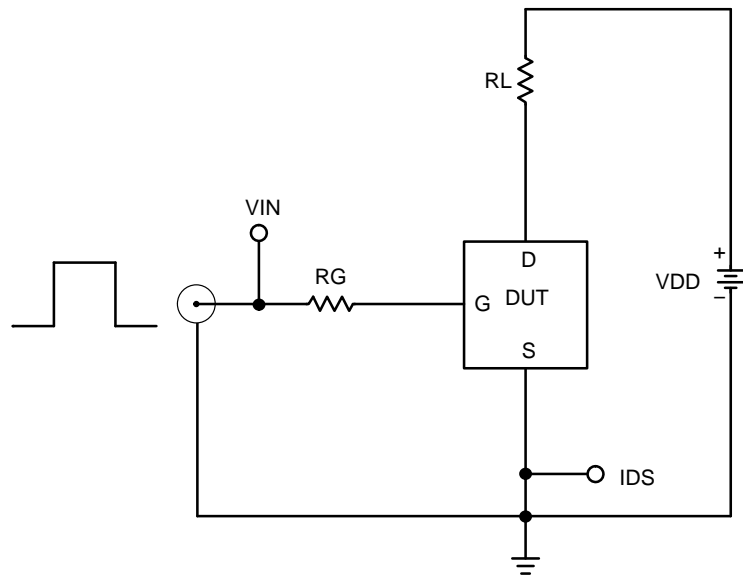
Drain-to-Source Voltage Internally Clamped		V _{DSS}	42	V
Drain-to-Gate Voltage Internally Clamped (R _G = 1.0 MΩ)		V _{DGR}	42	V
Gate-to-Source Voltage		V _{GS}	±14	V
Continuous Drain Current		I _D	Internally Limited	
Total Power Dissipation – SOT-223 Version	@ T _A = 25°C (Note 1)	P _D	1.1	W
	@ T _A = 25°C (Note 2)		1.74	
	@ T _S = 25°C		8.9	
Total Power Dissipation – DFN Version	@ T _A = 25°C (Note 1)	P _D	0.76	W
	@ T _A = 25°C (Note 2)		1.78	
	@ T _S = 25°C		8.9	



-









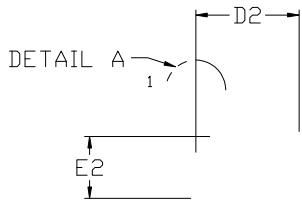
		†
NCV8402STT1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
NCV8402ASTT1G		
NCV8402STT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV8402ASTT3G		
NCV8402AMNT2G	DFN6 (Pb-Free)	2000 / Tape & Reel
NCV8402AMNWT1G	DFN6 (Pb-Free, Wettable Flank)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

CASE 506AX
ISSUE A

DATE 22 SEP 2020



NOTE 3

⊕	0.10	C	A	B
	0.05	C		

BOTTOM VIEW

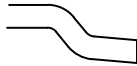
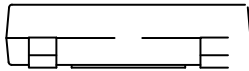
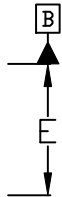




SCALE 1:1

SOT-223 (TO-261)
CASE 318E 04
ISSUE R

DATE 02 OCT 2018



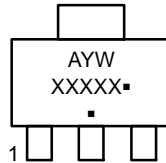
MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b			
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		

SOT-223 (TO-261)
CASE 318E 04
ISSUE R

DATE 02 OCT 2018

- | | | | | |
|---|--|--|--|--|
| LE 1:
IN 1. BA E
2. C LLEC
3. EMI E
4. C LLEC | LE 2:
IN 1. AN DE
2. CA H DE
3. NC
4. CA H DE | LE 3:
IN 1. GA E
2. DAIN
3. CE
4. DAIN | LE 4:
IN 1. CE
2. DAIN
3. GA E
4. DAIN | LE 5:
IN 1. DAIN
2. GA E
3. CE
4. GA E |
| LE 6:
IN 1. E
2. IN
3.
4. IN | LE 7:
IN 1. AN DE 1
2. CA H DE
3. AN DE 2
4. CA H DE | LE 8:
CANCELLED | LE 9:
IN 1. IN
2. GAND
3. L G
4. GAND | LE 10:
IN 1. CA H DE
2. AN DE
3. GA E
4. AN DE |
| LE 11:
IN 1. M 1
2. M 2
3. GA E
4. M 2 | LE 12:
IN 1. IN
2.
3. NG
4. | LE 13:
IN 1. GA E
2. C LLEC
3. EMI E
4. C LLEC | | |

**GENERIC
MARKING DIAGRAM***



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-223 (TO-261)	PAGE 2 OF 2

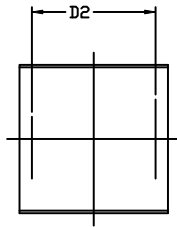
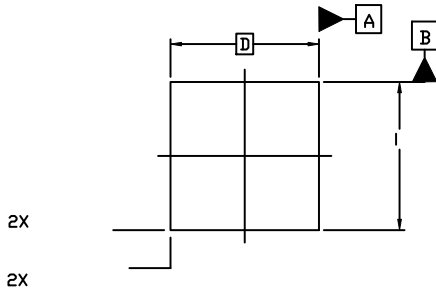
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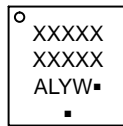
SCALE 2:1

DFNW6 3x3, 0.95P
CASE 506DK
ISSUE A

DATE 07 MAY 2021



**GENERIC
MARKING DIAGRAM***



XXXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot

Y = Year

W = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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